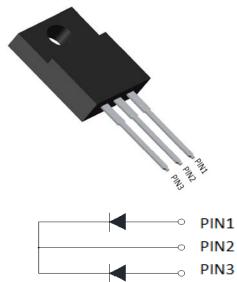




# **Schottky Diodes**



#### **Features**

- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Solder dip 275 °C max. 7 s, per JESD 22-B106

#### **Typical Applications**

Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

#### **Mechanical Data**

• Package: ITO-220AB

Molding compound meets UL 94 V-0 flammability rating, RoHS-compliant

• Terminals: Tin plated leads, solderable per J-STD-

002 and JESD22-B102
• Polarity: As marked

# ■Maximum Ratings (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	MBR3045FCT
Device marking code			MBR3045FCT
Repetitive Peak Reverse Voltage	VRRM	V	45
Average Rectified Output Current @60Hz sine wave, R-load, Ta=25°C	lo	А	30
Surge(Non-repetitive)Forward Current @60Hz half sine-wave,1 cycle, Ta=25°C	IFSM	А	250
Current Squared Time @1ms≤t<8.3ms Tj=25℃,	l <sup>2</sup> t	A <sup>2</sup> s	262
Storage Temperature	Tstg	$^{\circ}\!$	-55 ~ <b>+</b> 150
Junction Temperature	Tj	°C	-55 ~ <b>+</b> 150

# **■Electrical Characteristics** (Ta=25°C Unless otherwise specified)

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	MBR3045FCT
Maximum instantaneous forward voltage drop per diode	VFM	V	IFM=15.0A	0.6
Maximum DC reverse current at	IRRM1	mA	VRM=VRRM T <sub>a</sub> =25℃	0.2
rated DC blocking voltage per diode	IRRM2		VRM=VRRM T <sub>a</sub> =100℃	100

Note1:Pulse test:300uS pulse widh,1% duty cycle

Note2:Pulse test:pulse widh 40mS

## MBR3045FCT

### **■Thermal Characteristics** (T<sub>a</sub>=25°C Unless otherwise specified)

PARAMETER		SYMBOL	UNIT	MBR3045FCT
Thermal Resistance	Between junction and case	R <sub>0</sub> J-C	°C <b>M</b>	4.0

### **■Ordering Information** (Example)

PREFERED P/N	UNIT WEIGHT(g)	MINIIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
MBR3045FCT	Approximate 1.6	50	1000	5000	Tube

# **■Characteristics** (Typical)

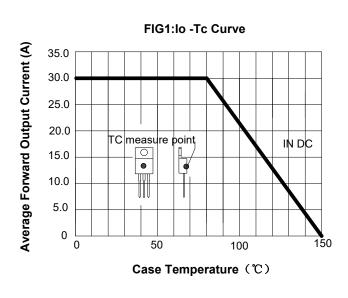


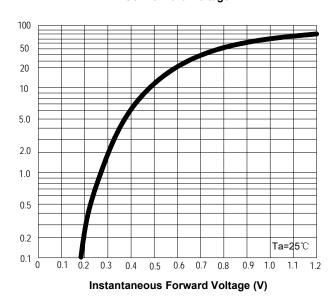
FIG2:Surge Forward Current Capability

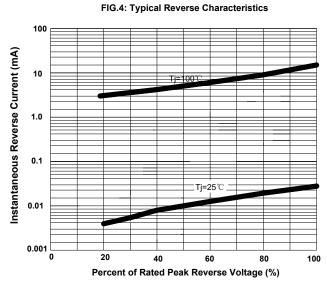
300
250
200
8.3ms Single
Half Sine-Wave
JEDEC Method

100
1 2 5 10 20 50 100

Number of Cycles

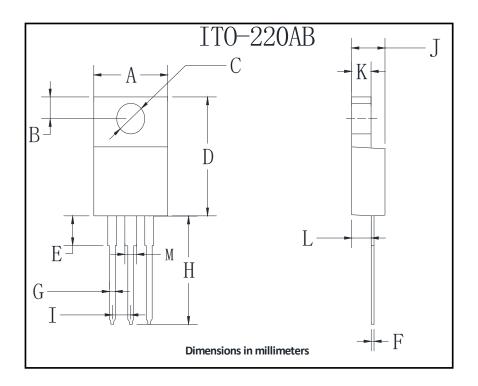
FIG3: Forward Voltage







#### **■Outline Dimensions**



ITO-220AB				
Dim	Min	Max		
Α	9.8	10.2		
В	2.25	2.75		
С	2.95	3.45		
D	14.75	15.25		
Е	3.05	3.95		
F	0.45	0.75		
G	0.45	0.75		
Н	13.4	14.2		
I	2.35	2.75		
J	4.3	4.8		
K	2.58	2.82		
L	2.58	2.82		
M	1.47	1.77		

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